

OptiMOS™2 Power-Transistor
Features

- Very low gate charge for high frequency applications
- Optimized for dc-dc conversion
- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target application
- Halogen-free according to IEC61249-2-21

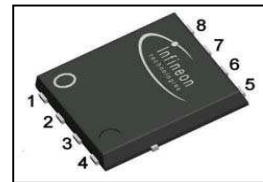


Halogen-Free

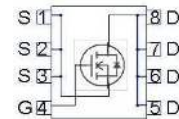
Product Summary

| | | |
|------------------|------|----|
| V_{DS} | 100 | V |
| $R_{DS(on),max}$ | 25.2 | mΩ |
| I_D | 40 | A |

PG-TDSON-8



| Type | Package | Marking |
|----------------|------------|----------|
| BSC252N10NSF G | PG-TDSON-8 | 252N10NS |


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|-------------------------------------|-------------------|---|-------------|------|
| Continuous drain current | I_D | $T_C=25\text{ °C}$ | 40 | A |
| | | $T_C=100\text{ °C}$ | 25 | |
| | | $T_A=25\text{ °C}$, $R_{thJA}=50\text{ K/W}^{2)}$ | 7.2 | |
| Pulsed drain current ³⁾ | $I_{D,pulse}$ | $T_C=25\text{ °C}$ | 160 | |
| Avalanche energy, single pulse | E_{AS} | $I_D=40\text{ A}$, $R_{GS}=25\text{ }\Omega$ | 68 | mJ |
| Gate source voltage | V_{GS} | | ± 20 | V |
| Power dissipation | P_{tot} | $T_C=25\text{ °C}$ | 78 | W |
| Operating and storage temperature | T_j , T_{stg} | | -55 ... 150 | °C |
| IEC climatic category; DIN IEC 68-1 | | | 55/150/56 | |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|--|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case | R_{thJC} | bottom | - | - | 1.6 | K/W |
| | | top | - | - | 18 | |
| Thermal resistance, junction - ambient | R_{thJA} | minimal footprint | - | - | 62 | |
| | | 6 cm ² cooling area ²⁾ | - | - | 50 | |

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified
Static characteristics

| | | | | | | |
|----------------------------------|---------------|---|-----|------|------|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$ | 100 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=43\text{ }\mu\text{A}$ | 2 | 3 | 4 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$ | - | 0.01 | 1 | μA |
| | | $V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$ | - | 10 | 100 | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$ | - | 1 | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}, I_D=20\text{ A}$ | - | 19.5 | 25.2 | m Ω |
| Gate resistance | R_G | | - | 1.6 | - | Ω |
| Transconductance | g_{fs} | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=40\text{ A}$ | 18 | 35 | - | S |

¹⁾J-STD20 and JESD22

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ see figure 3

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|------------------------------|--------------|---|---|-----|------|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$ $f=1\text{ MHz}$ | - | 860 | 1100 | pF |
| Output capacitance | C_{oss} | | - | 280 | 370 | |
| Reverse transfer capacitance | C_{rss} | | - | 10 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=25\text{ A}, R_G=1.6\ \Omega$ | - | 11 | - | ns |
| Rise time | t_r | | - | 21 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 16 | - | |
| Fall time | t_f | | - | 4 | - | |

Gate Charge Characteristics⁴⁾

| | | | | | | |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=50\text{ V}, I_D=25\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 5 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 3 | - | |
| Switching charge | Q_{sw} | | - | 6 | - | |
| Gate charge total | Q_g | | - | 13 | 17 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5.8 | - | V |
| Output charge | Q_{oss} | $V_{DD}=50\text{ V}, V_{GS}=0\text{ V}$ | - | 28 | 38 | nC |

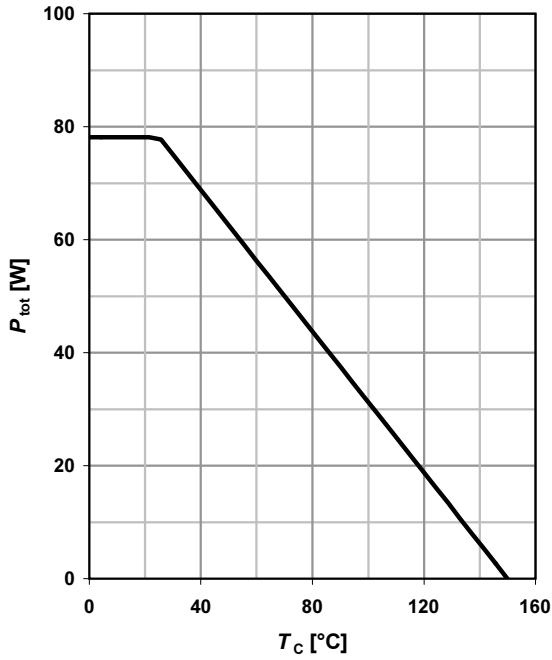
Reverse Diode

| | | | | | | |
|----------------------------------|---------------|---|---|-----|-----|----|
| Diode continuous forward current | I_S | $T_C=25\text{ }^\circ\text{C}$ | - | - | 40 | A |
| Diode pulse current | $I_{S,pulse}$ | | - | - | 160 | |
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=40\text{ A},$ $T_j=25\text{ }^\circ\text{C}$ | - | 0.9 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=50\text{ V}, I_F=25\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 82 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 198 | - | nC |

⁴⁾ See figure 16 for gate charge parameter definition

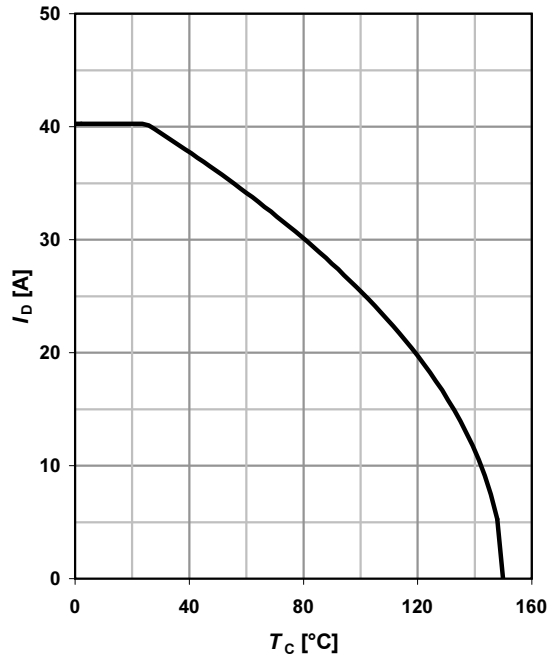
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

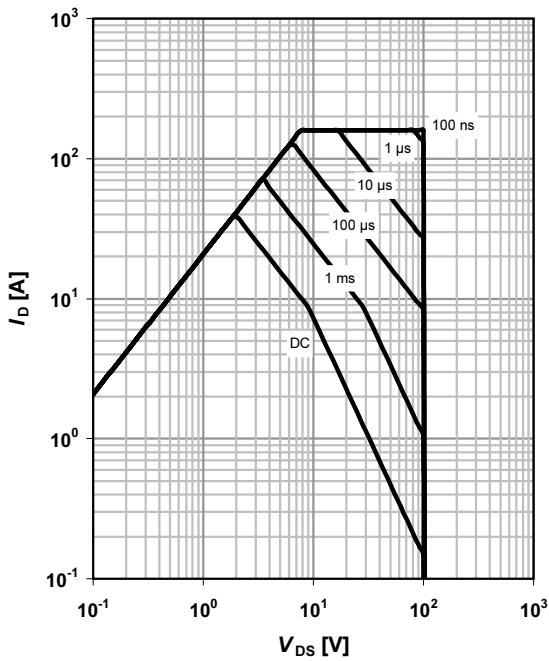
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



3 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

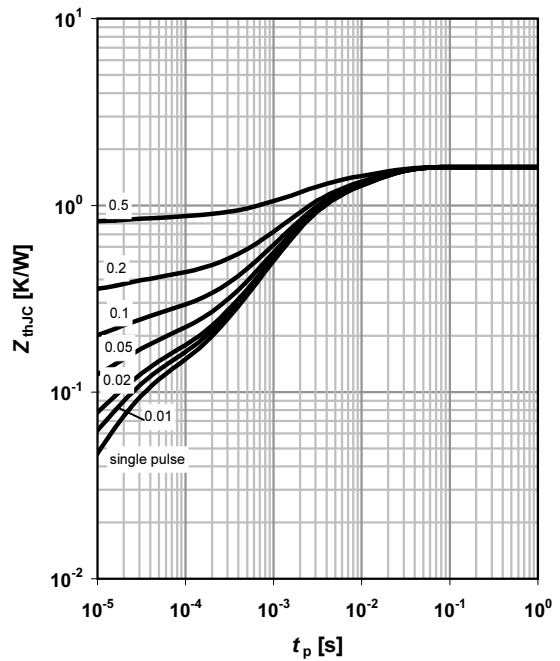
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

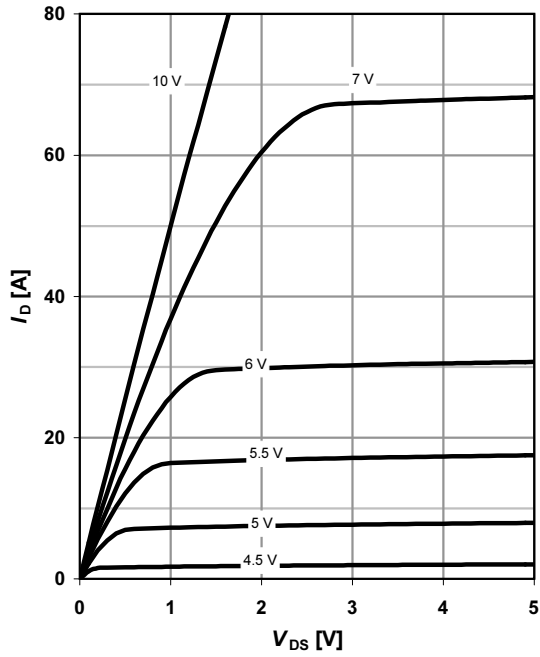
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

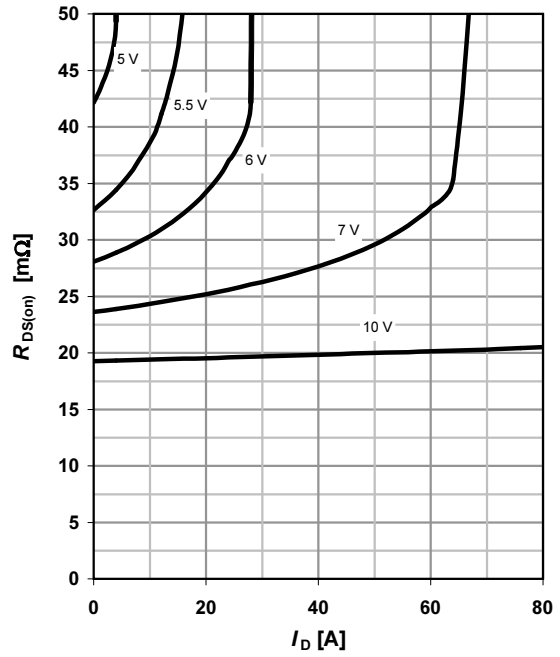
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

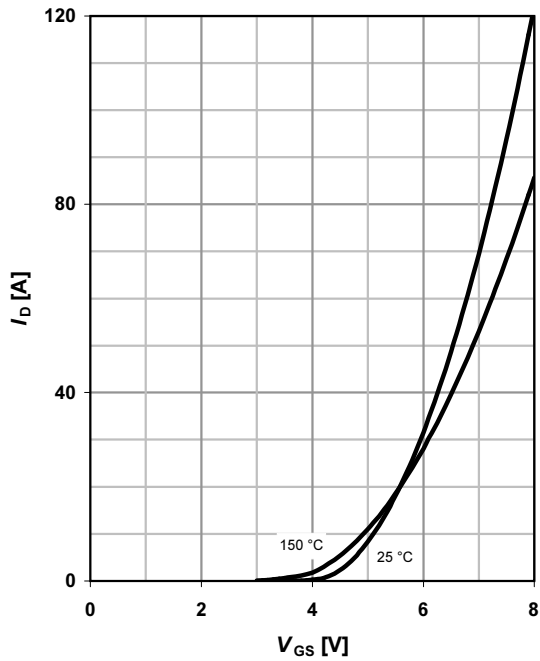
parameter: V_{GS}



7 Typ. transfer characteristics

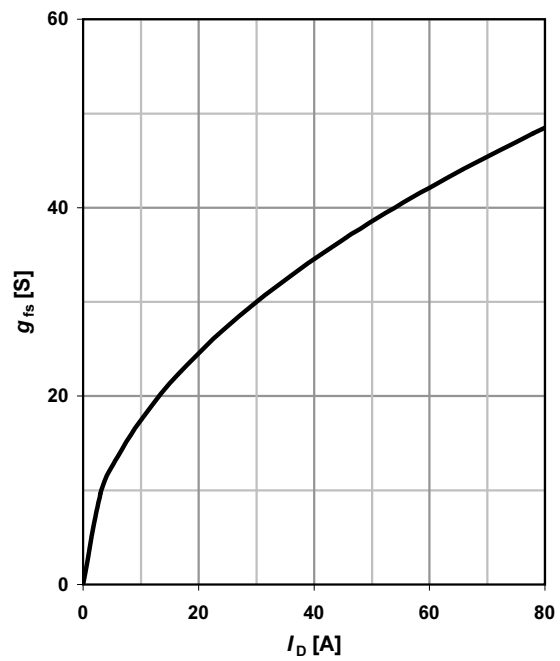
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



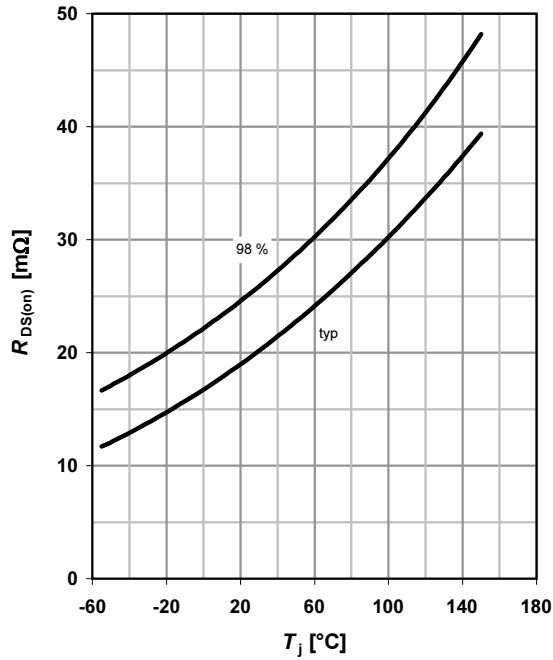
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



9 Drain-source on-state resistance

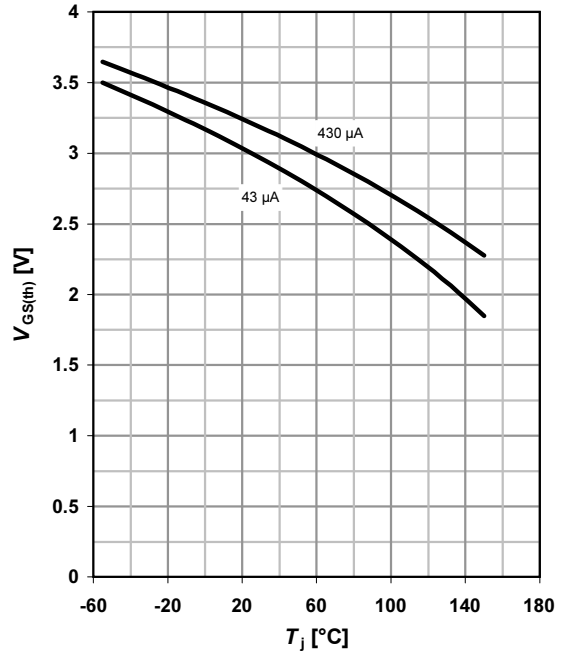
$R_{DS(on)} = f(T_j); I_D = 40 \text{ A}; V_{GS} = 10 \text{ V}$



10 Typ. gate threshold voltage

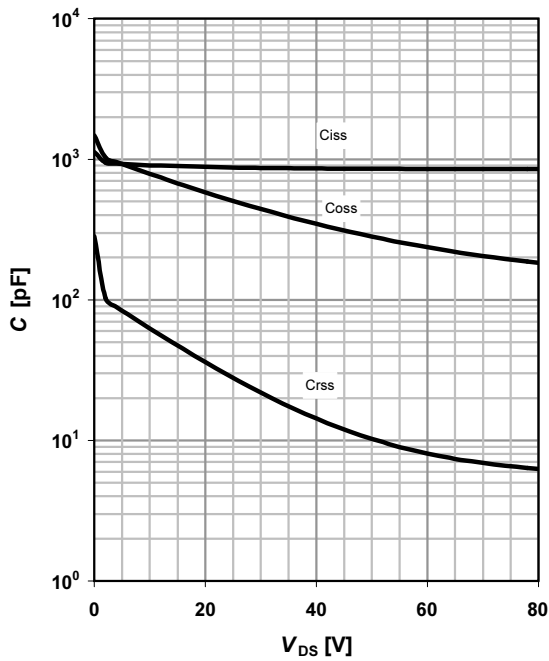
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



11 Typ. capacitances

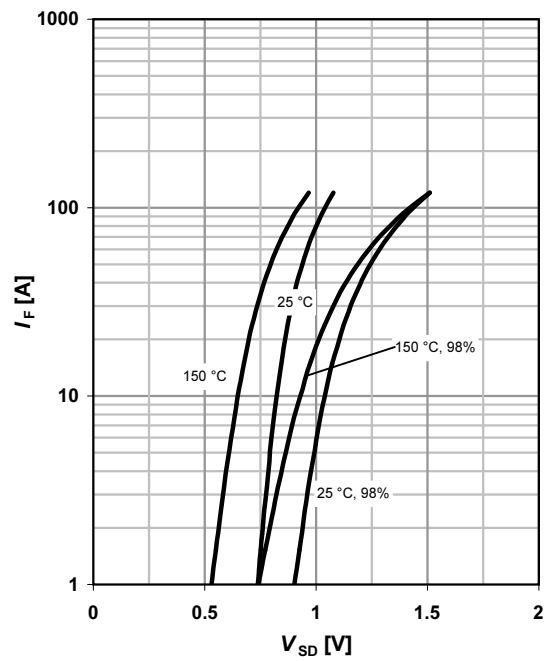
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

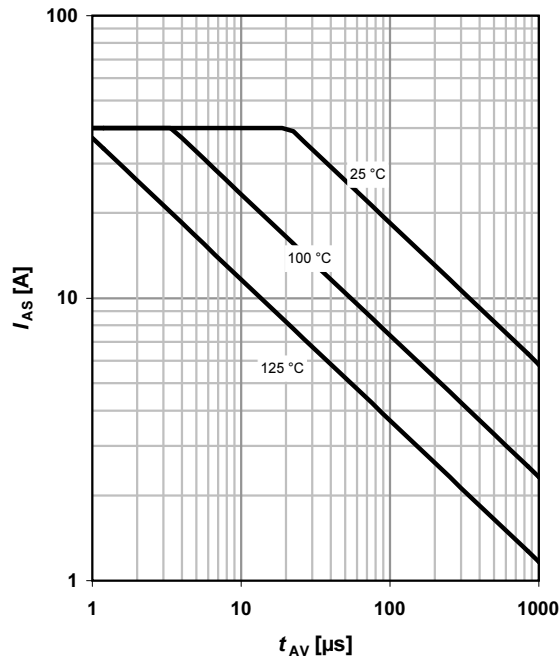
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

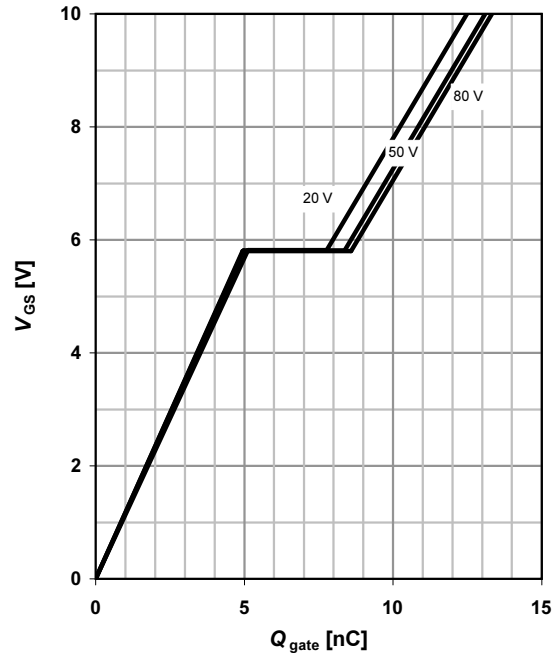
parameter: $T_{j(start)}$



14 Typ. gate charge

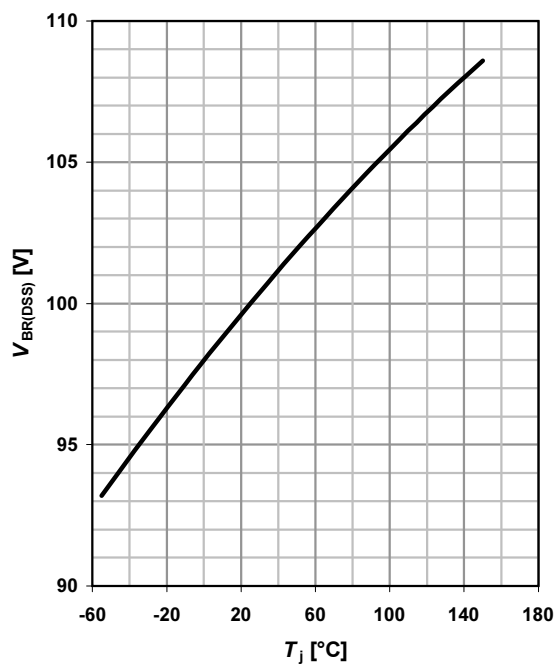
$V_{GS}=f(Q_{gate}); I_D=25 \text{ A pulsed}$

parameter: V_{DD}

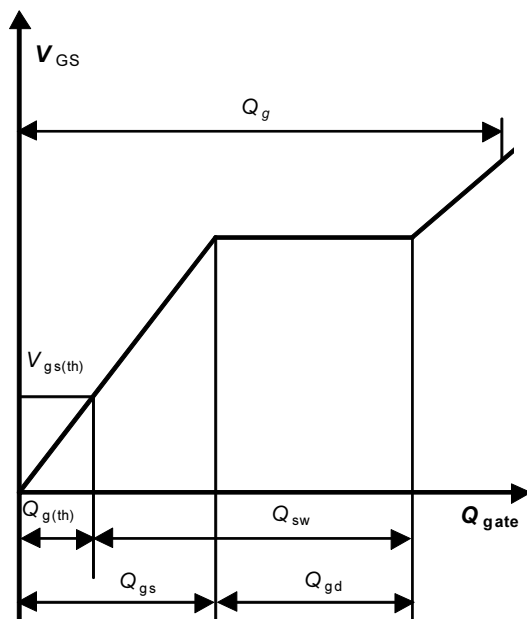


15 Drain-source breakdown voltage

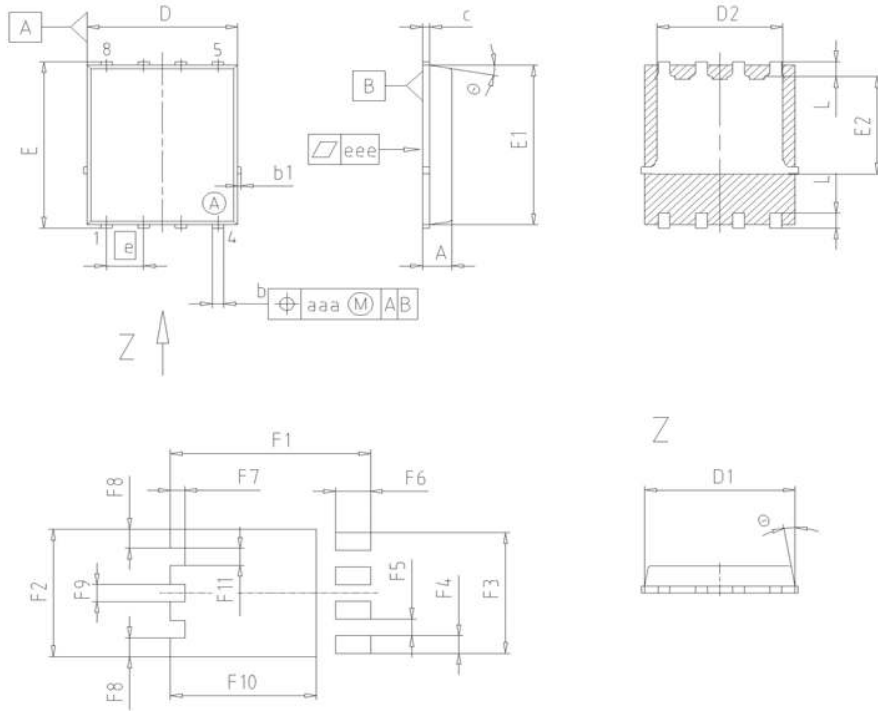
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



16 Gate charge waveforms



Package Outline: PG-TDSON-8



| DIM | MILLIMETERS | | INCHES | |
|------|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.90 | 1.10 | 0.035 | 0.043 |
| b | 0.34 | 0.54 | 0.013 | 0.021 |
| b1 | 0.02 | 0.22 | 0.001 | 0.008 |
| c | 0.15 | 0.35 | 0.006 | 0.014 |
| D=D1 | 4.95 | 5.35 | 0.195 | 0.211 |
| D2 | 4.20 | 4.40 | 0.165 | 0.173 |
| E | 5.95 | 6.35 | 0.234 | 0.250 |
| E1 | 5.70 | 6.10 | 0.224 | 0.240 |
| E2 | 3.40 | 3.80 | 0.134 | 0.150 |
| e | 1.27 | | 0.050 | |
| N | 8 | | 8 | |
| L | 0.45 | 0.65 | 0.018 | 0.026 |
| □ | 8.5° | 11.5° | 8.5° | 11.5° |
| aaa | 0.25 | | 0.010 | |
| eee | 0.05 | | 0.002 | |
| F1 | 6.75 | 6.95 | 0.266 | 0.274 |
| F2 | 4.60 | 4.80 | 0.181 | 0.189 |
| F3 | 4.36 | 4.56 | 0.172 | 0.180 |
| F4 | 0.55 | 0.75 | 0.022 | 0.030 |
| F5 | 0.52 | 0.72 | 0.020 | 0.028 |
| F6 | 1.10 | 1.30 | 0.043 | 0.051 |
| F7 | 0.40 | 0.60 | 0.016 | 0.024 |
| F8 | 0.60 | 0.80 | 0.024 | 0.031 |
| F9 | 0.53 | 0.73 | 0.021 | 0.029 |
| F10 | 4.90 | 5.10 | 0.193 | 0.201 |
| F11 | 0.53 | 0.73 | 0.021 | 0.029 |

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